

	Hits	Search Text	DBs	Time Stamp
1	2	"6853006".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 20:49
2	83051	silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 20:55
3	1947	silicon adj carbide adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:29
4	359	silicon adj carbide adj substrate and metal with contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:06
5	14	silicon adj carbide adj substrate and metal with contact same heat adj treatment	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:25
6	2	"20040214453"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:11
7	2	jp-2000012846-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:19
8	2	jp-10125620-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:16
9	4	("5442200" "5502003").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:19

	Hits	Search Text	DBs	Time Stamp
10	2	jp-08064800-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:20
11	191	silicon adj carbide adj substrate and heat adj treatment	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:42
12	60	silicon adj carbide adj substrate same heat adj treatment	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/06 21:42
13	27	silicon adj carbide adj substrate and metal and (etch etching etched) with ((sulfuric adj acid) (phosphoric adj acid) (nitric adj acid) (acetic adj acid) (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:31
14	3	silicon adj carbide adj substrate and metal same (etch etching etched) with ((sulfuric adj acid) (phosphoric adj acid) (nitric adj acid) (acetic adj acid) (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:34
15	0	silicon adj carbide adj substrate and metal same (etch etching etched) with ((sulfuric adj acid) (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:34
16	9	silicon adj carbide adj substrate and metal and (etch etching etched) with ((sulfuric adj acid) (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:35
17	2	silicon adj carbide adj substrate and metal and (etch etching etched) with ((sulfuric adj acid) with (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:35

	Hits	Search Text	DBs	Time Stamp
18	312	substrate and metal same (etch etching etched) with ((sulfuric adj acid) with (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:35
19	145	substrate and metal with (etch etching etched) with ((sulfuric adj acid) with (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:36
20	58	substrate and metal with (etch etching etched) with ((sulfuric adj acid) with (hydrogen adj peroxide)) and metal with (insulator insulation insulating dielectric) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:37
21	35	substrate and metal with (etch etching etched) with ((sulfuric adj acid) with (hydrogen adj peroxide)) and metal with (insulator insulation insulating dielectric) with contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/08/07 17:37